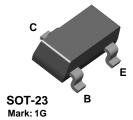


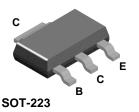
# MPSA06

## MMBTA06

## PZTA06







# **NPN General Purpose Amplifier**

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 33.

### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	80	V
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
I <sub>C</sub>	Collector Current - Continuous	500	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### **Thermal Characteristics** TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units	
		MPSA06	*MMBTA06	**PZTA06	
$P_D$	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	1,000 8.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

<sup>1)</sup> These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

<sup>\*\*</sup>Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>.

### **NPN General Purpose Amplifier**

(continued)

#### **Electrical Characteristics**

TA = 25°C unless otherwise noted

Parameter	Test Conditions	Min	Max	Units
PACTERISTICS				
Collector-Emitter Sustaining Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	80		V
Emitter-Base Breakdown Voltage	$I_E = 100  \mu A,  I_C = 0$	4.0		V
Collector-Cutoff Current	$V_{CE} = 60 \text{ V}, I_{B} = 0$		0.1	μΑ
Collector-Cutoff Current	$V_{CB} = 80 \text{ V}, I_{E} = 0$		0.1	μΑ
	RACTERISTICS  Collector-Emitter Sustaining Voltage*  Emitter-Base Breakdown Voltage  Collector-Cutoff Current	RACTERISTICS  Collector-Emitter Sustaining Voltage* $I_C = 1.0 \text{ mA}, I_B = 0$ Emitter-Base Breakdown Voltage $I_E = 100 \mu\text{A}, I_C = 0$ Collector-Cutoff Current $V_{CE} = 60 \text{ V}, I_B = 0$	RACTERISTICS  Collector-Emitter Sustaining Voltage* $I_C = 1.0 \text{ mA}, I_B = 0$ 80  Emitter-Base Breakdown Voltage $I_E = 100 \mu\text{A}, I_C = 0$ 4.0  Collector-Cutoff Current $V_{CE} = 60 \text{ V}, I_B = 0$	RACTERISTICS  Collector-Emitter Sustaining Voltage* $I_C = 1.0 \text{ mA}, I_B = 0$ 80  Emitter-Base Breakdown Voltage $I_E = 100 \mu\text{A}, I_C = 0$ 4.0  Collector-Cutoff Current $V_{CE} = 60 \text{ V}, I_B = 0$ 0.1

#### **ON CHARACTERISTICS**

$h_{FE}$	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	100		
		$I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$	100		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.25	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$		1.2	V

#### SMALL SIGNAL CHARACTERISTICS

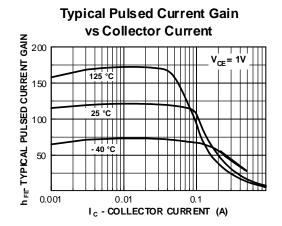
f⊤	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 2.0 \text{ V},$	100	MHz
		f = 100 MHz		

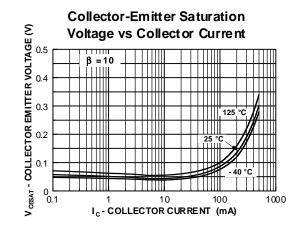
<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

#### **Spice Model**

NPN (Is=8.324f Xti=3 Eg=1.11 Vaf=100 Bf=12.16K Ne=1.368 Ise=73.27f lkf=.1096 Xtb=1.5 Br=11.1 Nc=2 Isc=0 lkr=0 Rc=.25 Cjc=18.36p Mjc=.3843 Vjc=.75 Fc=.5 Cje=55.61p Mje=.3834 Vje=.75 Tr=72.15n Tf=516.1p ltf=.5 Vtf=4 Xtf=6 Rb=10)

### **Typical Characteristics**

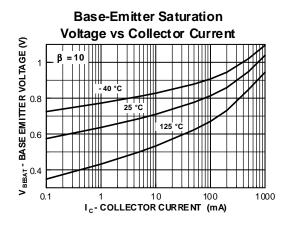


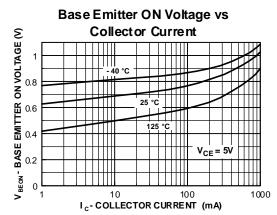


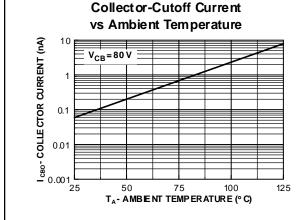
#### **NPN General Purpose Amplifier**

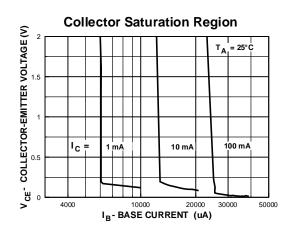
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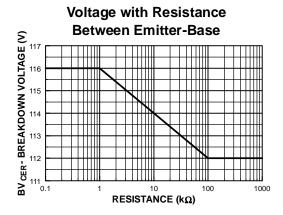
#### Typical Characteristics (continued)



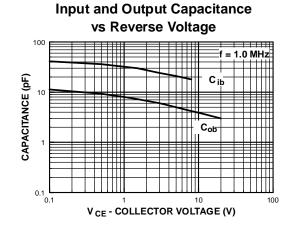








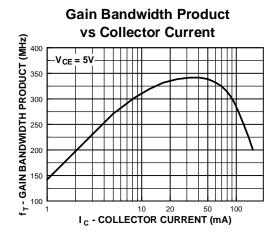
**Collector-Emitter Breakdown** 

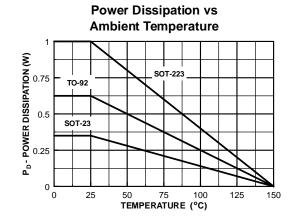


# **NPN General Purpose Amplifier**

(continued)

# Typical Characteristics (continued)

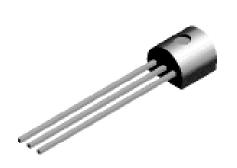


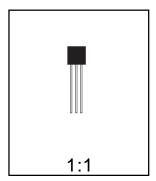


## **TO-92 Package Dimensions**



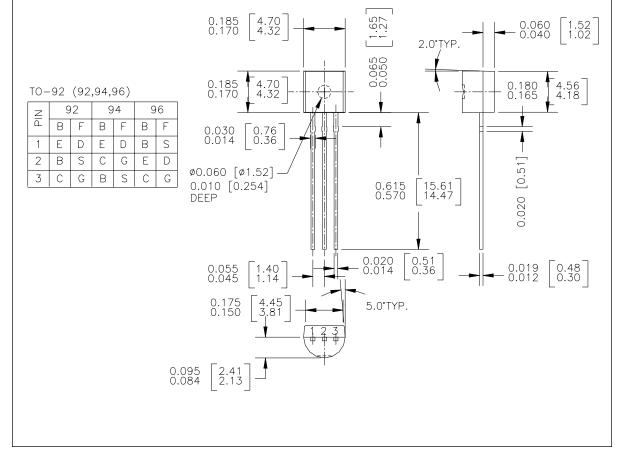
# TO-92 (FS PKG Code 92, 94, 96)





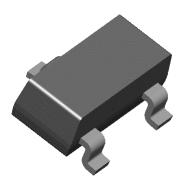
Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

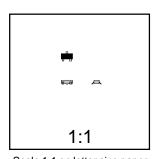
Part Weight per unit (gram): 0.1977





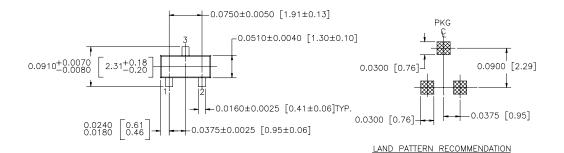
# SOT-23 (FS PKG Code 49)

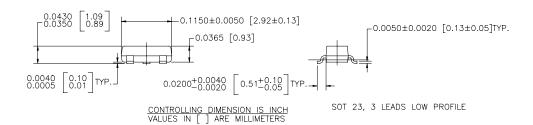




Scale 1:1 on letter size paper Dimensions shown below are in:

inches [millimeters]
Part Weight per unit (gram): 0.0082



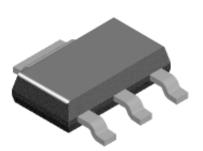


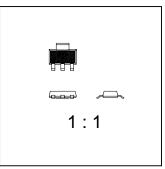
NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993



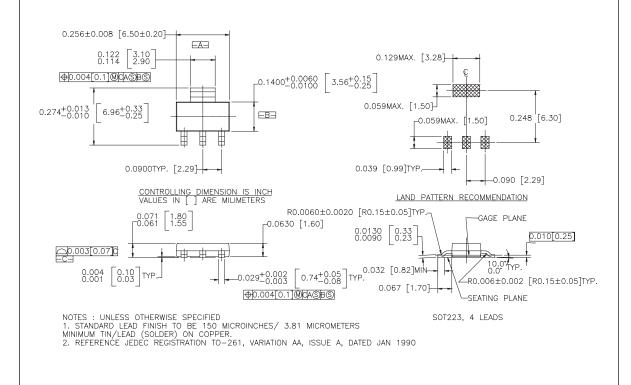
# SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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